

超新星起源プレソラー SiC粒子の形成

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1-1. Presolar grains

○ Presolar grains

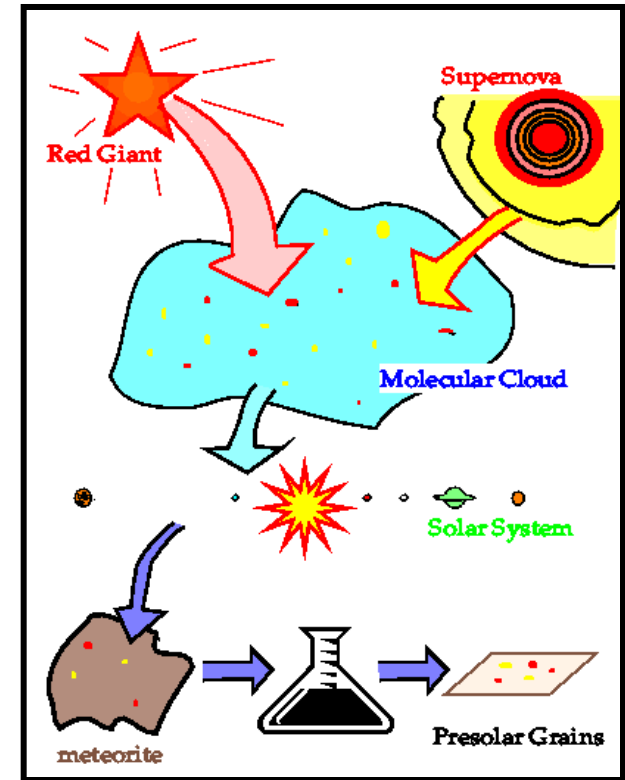
- discovered in primitive meteorites
- showing peculiar isotopic compositions
(different from the solar system's materials)
- thought to have formed in stars before the Sun was formed

→ offering key information on

- nuclear processes in the parent stars
- physical conditions in which they formed

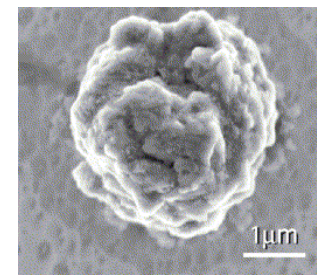
- abundance (volume fraction): ~100-500 ppm (~0.1-0.5 %)
- mineral composition

graphite, **SiC**, TiC, Si₃N₄, Al₂O₃, MgAl₂O₄, Mg₂SiO₄, MgSiO₃ ...



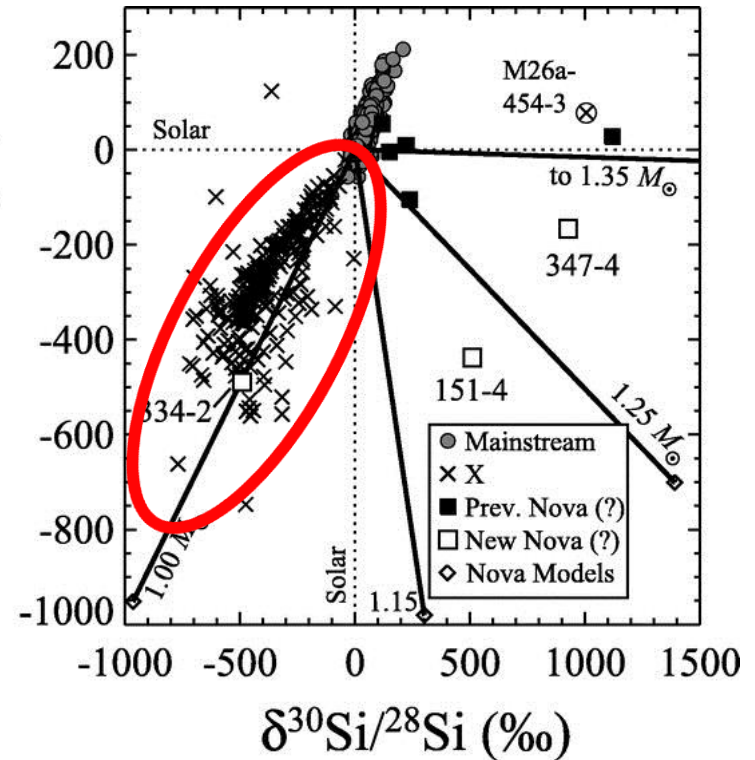
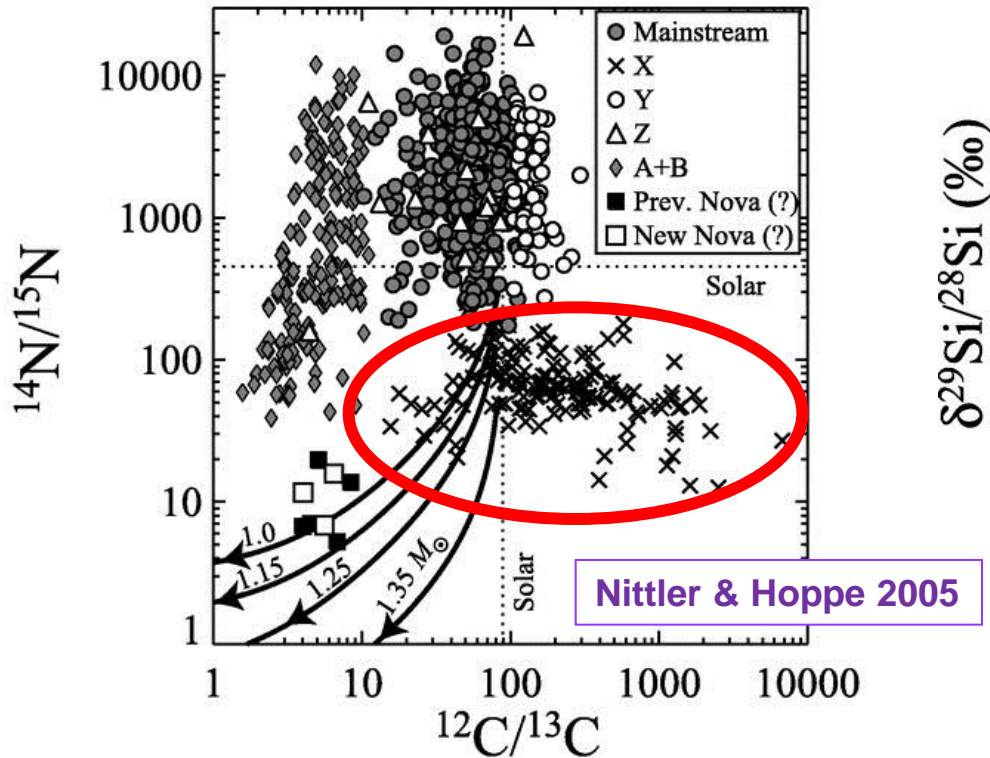
<http://presolargrains.net/>

1-2. Presolar Type X SiC grains



Nittler 2003

○ Presolar SiC grains (~10 ppm)



○ Type X SiC grains (~0.1 ppm, size: 0.1-20 μm)

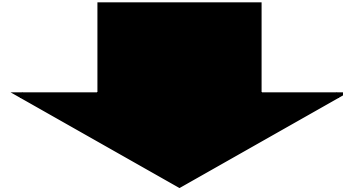
- $^{12}\text{C}/^{28}\text{Si}$ rich, with excesses in ^{44}Ca (^{44}Ti), ^{49}Ti (^{49}V)

→ originated from core-collapse supernovae

1-3. Long-lasting questions

○ Fact

A fraction of presolar SiC grains is highly likely SN-origin

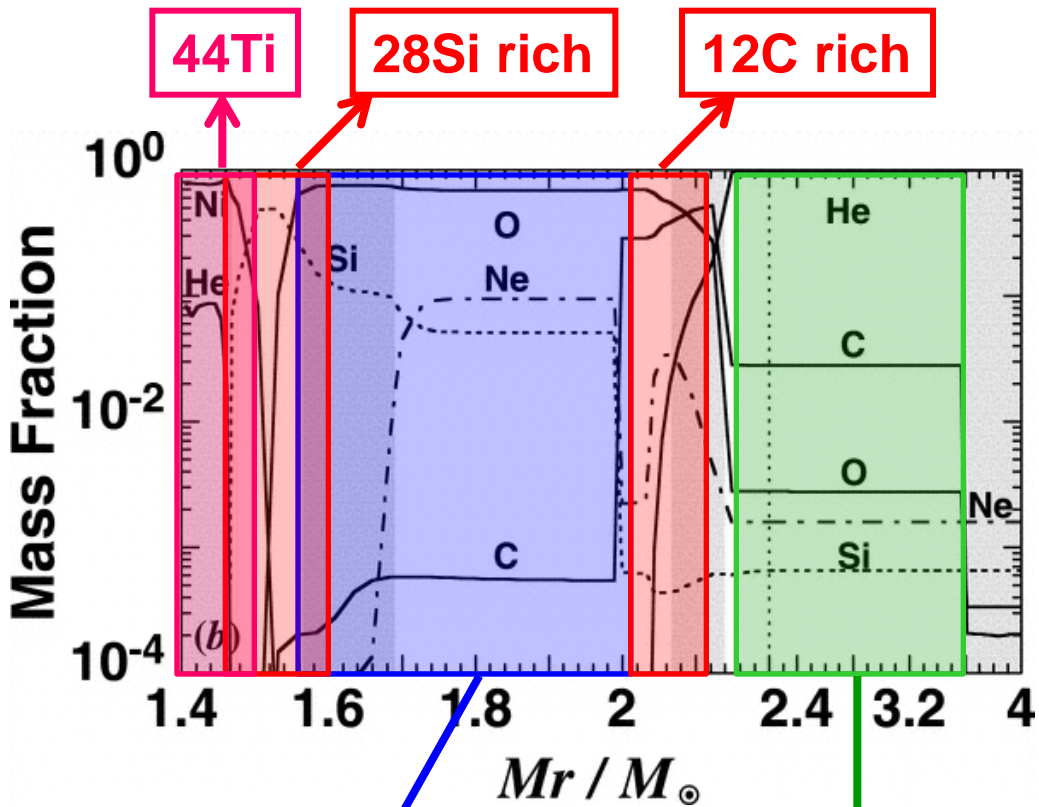


○ Question

How do these SiC grains form in the ejecta of core-collapse supernovae?

- ## Any theoretical studies have not yet realized the
- ## formation of SiC grains in supernovae

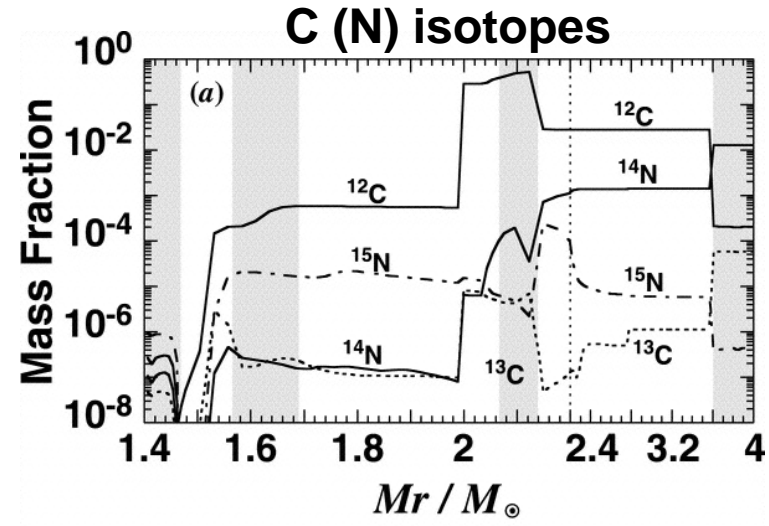
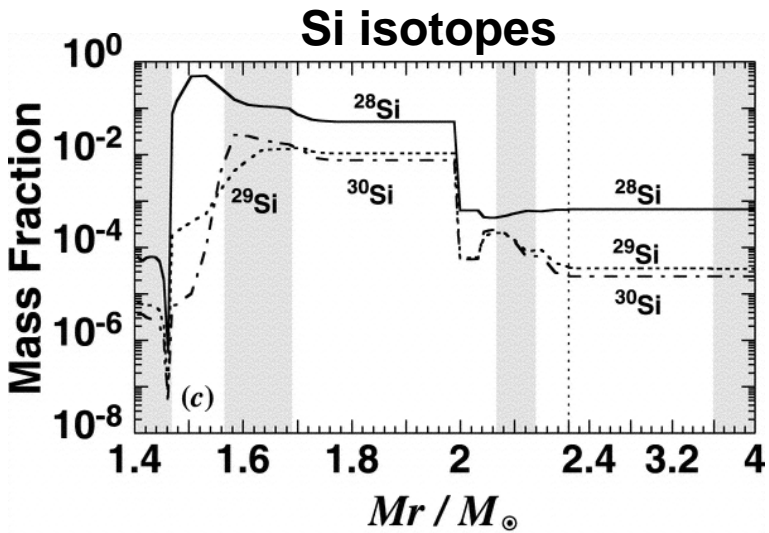
2-1. Elemental abundances in the SN ejecta



Yoshida 2007; 4 Msun He-core model ($M_{\text{star}} \sim 18 M_{\text{sun}}$)

**O-rich ($O/C \gg 1$)
29, 30Si rich**

**29, 30Si solar
14N rich**



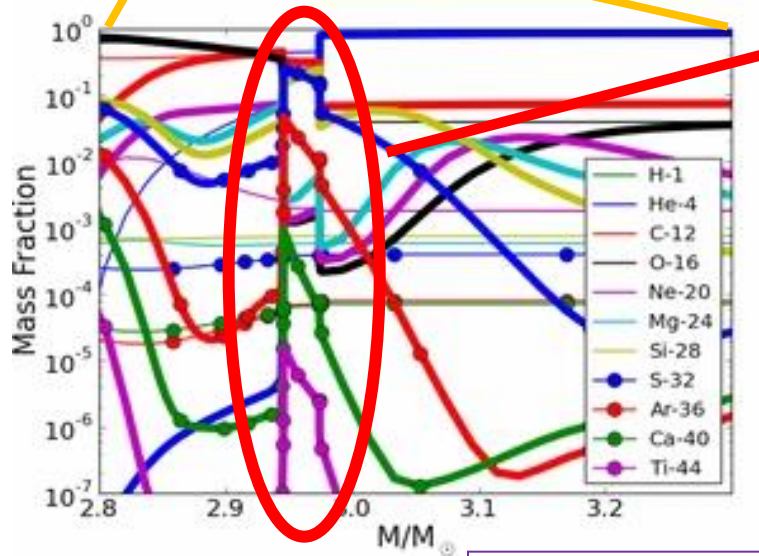
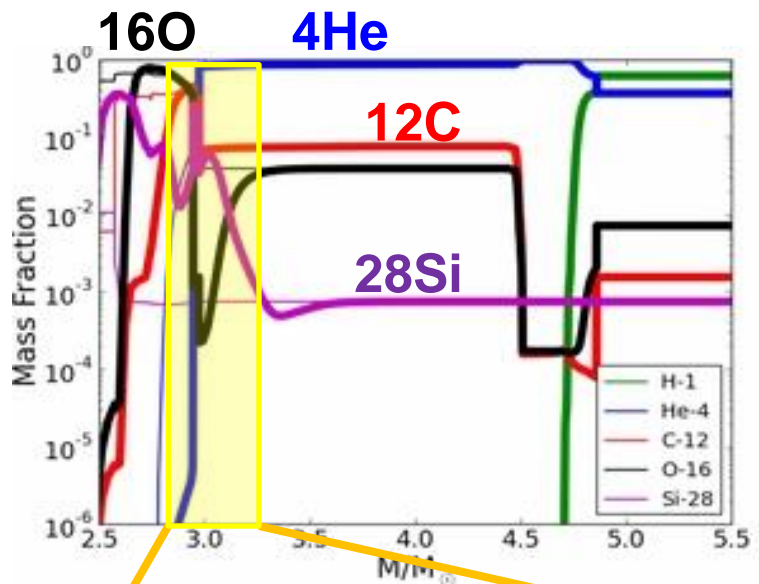
Needed unrealistic mixing of the ejecta

2-2. Possible formation site of SiC grains in SNe

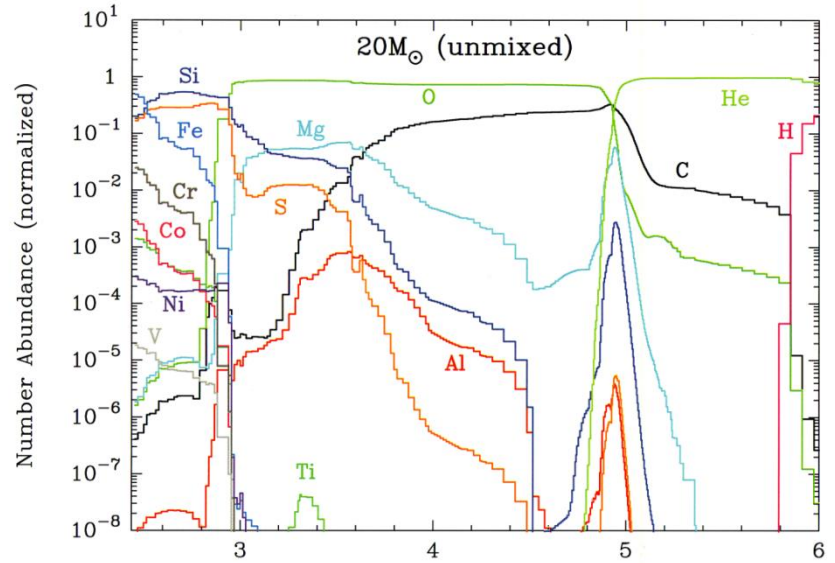
O Moderately energetic SNe

$E_{kin} = (3-5) \times 10^{51}$ erg
 (normal SNe : $E_{kin} \sim 1 \times 10^{51}$ erg)

explosive burning happens at the boundary between O-rich region and He-rich region



Pignatari+2013



Umeda & Nomoto 2002

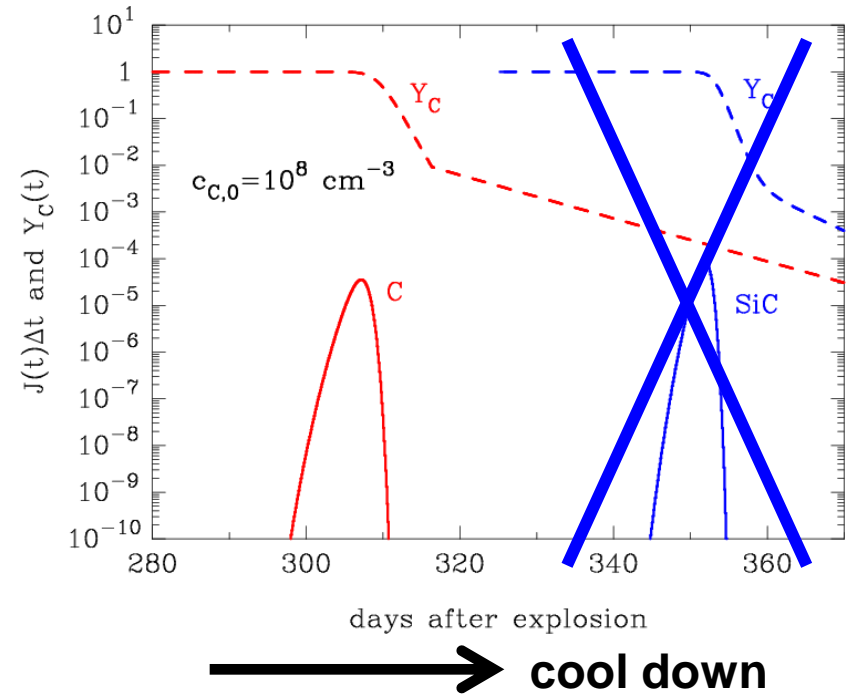
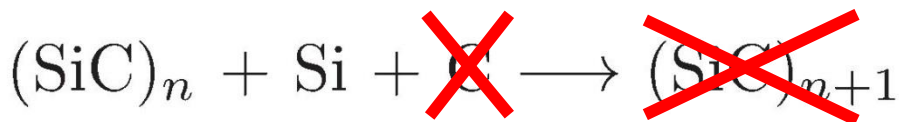
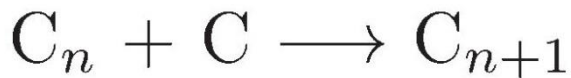
2-3. No formation of SiC in the calculations

○ Condensation temperature

- C grains : $T_{\text{con}} = 1700\text{-}2200$ K
- SiC grains: $T_{\text{con}} = 1300\text{-}1800$ K

→ In C/Si-rich gas, C grains first condense to use up the gas-phase C atoms

○ Formation path of grains



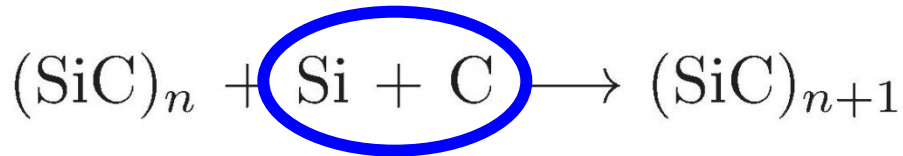
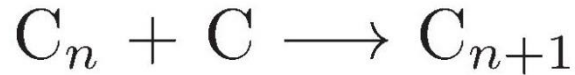
More efficient destruction of C grains (clusters)?

UV radiation, high-energy e, chemical reaction, ...

→ this may not do a good job

2-4. Formation of SiC grains via molecules

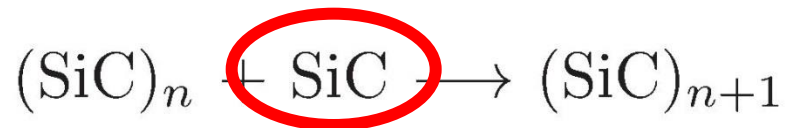
Previous works



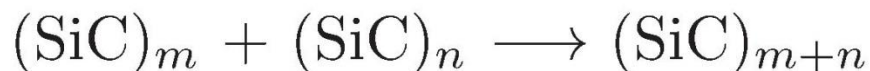
→ accretion of Si/C atoms

This work

- accretion of SiC molecules

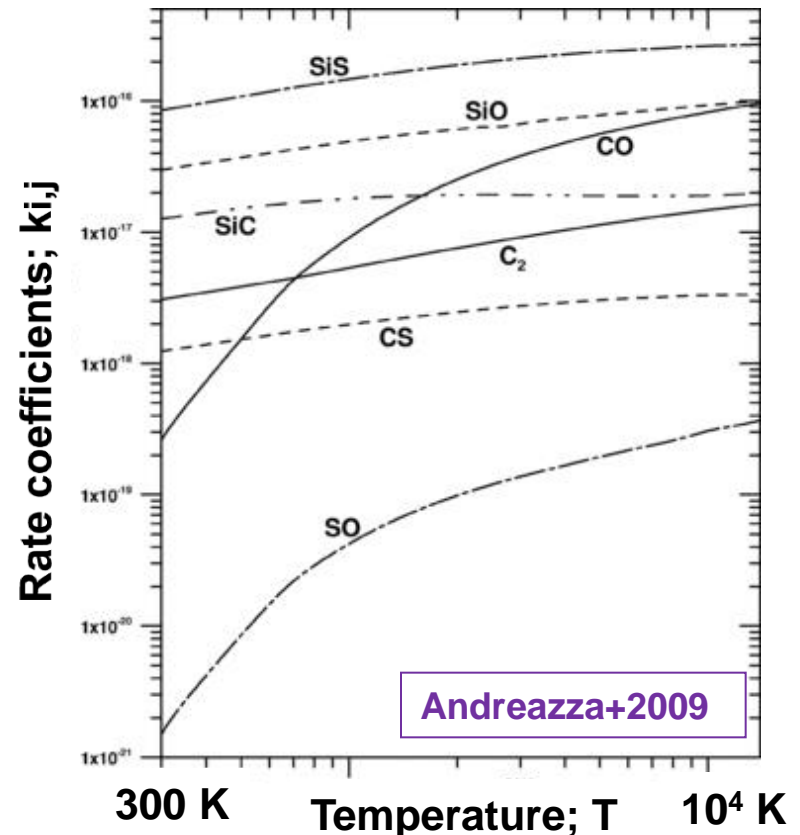


- coagulation

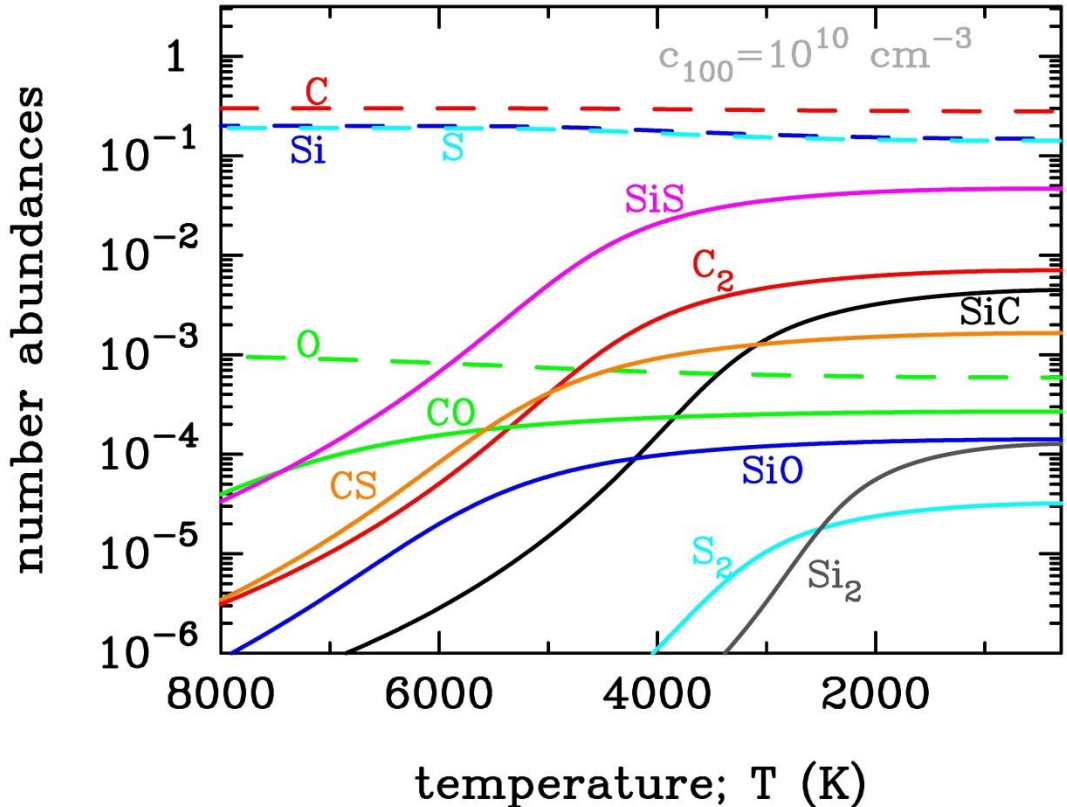


rate coefficients of radiative association of molecules $k_{i,j}$

$$\frac{dc_k^{\text{mol}}}{dt} = k_{ij}(T)c_i c_j$$



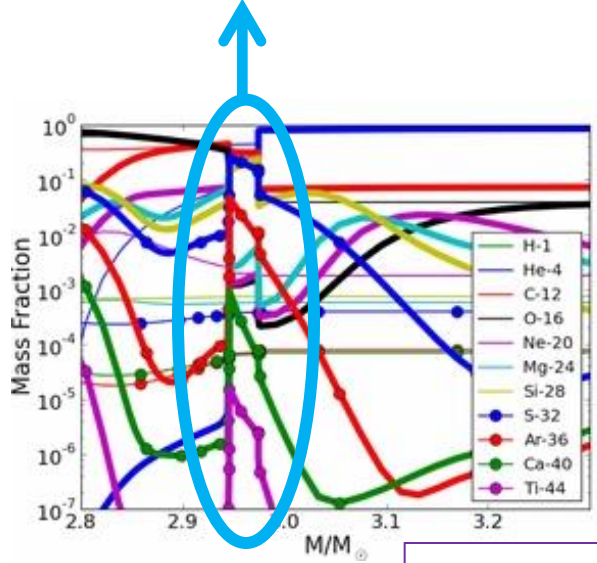
3-1. Formation of SiC molecules



$$c(t) = c_{100} \left(\frac{t}{100 \text{ day}} \right)^{-3} \text{ cm}^{-3}$$

$$T(t) = 10^4 \left(\frac{t}{100 \text{ day}} \right)^{-1} \text{ K}$$

Element	# abundance
He	0.3
C	0.3
O	0.001
Ne	0.001
Mg	0.002
Si	0.2
S	0.19
Ar	0.006



3-2. Equation of dust formation

○ Master equations of dust growth

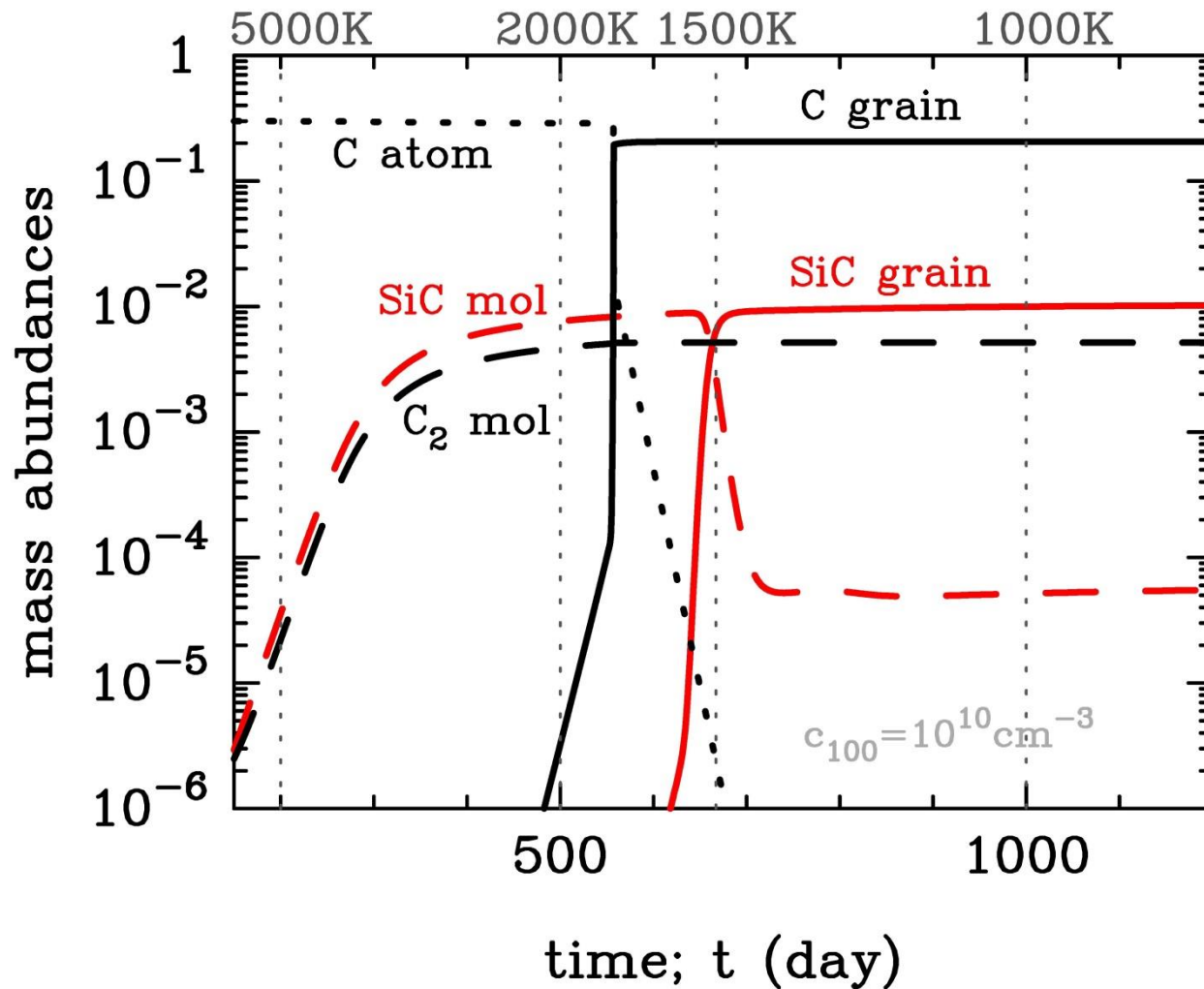
$$\frac{dc_n}{dt} = \frac{1}{2} \sum_{i=1}^{n-1} K_{i,n-i}(T) c_i (c_{n-i} - c_n e^{\gamma_{i,n-1}}) - c_n \sum_{l=1}^{n_{\max}} K_{n,l}(T) (c_l - c_{n+l} e^{\gamma_{l,n}})$$

$$K_{i,j}(T) = \alpha_s \pi (a_i + a_j)^2 \left(\frac{8kT}{\pi m_{i,j}} \right)^{\frac{1}{2}}$$

$$\gamma_{i,n-i}(T) = \frac{4\pi a_0^2 \sigma}{kT} \left[(n-1)^{\frac{2}{3}} - (n-i-1)^{\frac{2}{3}} - (i-1)^{\frac{2}{3}} \right] - \ln S_i$$

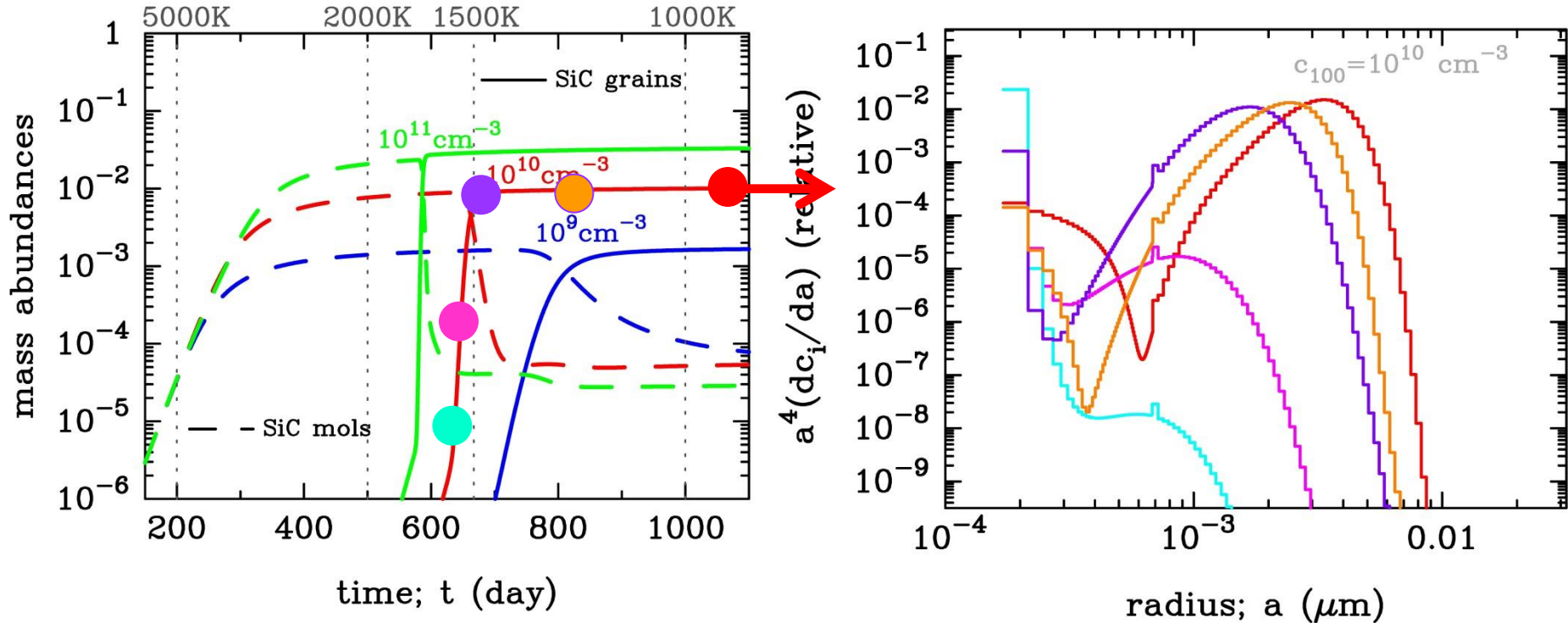
taking account of nucleation and grain growth through gas accretion and coagulation between grains simultaneously!

3-3. Can SiC grains form in the SN ejecta?



Yes, the formation of SiC grains is possible !

3-4. Formation process of SiC grains



○ Formation of SiC grains is possible !!

- Condensation temperature is higher for higher gas density
- Dust growth proceeds on a short timescale through rapid accretion of molecules
- Coagulation makes the average radius by about a factor of 2

3-5. Size distribution of SiC grains formed

○ Timescale of collision

$$\tau_{\text{coll}}^{-1} = \pi S_{i,j} \langle v \rangle c_i$$

– Timescale of gas accretion onto 0.001 μm -sized grains

$$\tau_{\text{acc}} \simeq 0.028 \text{ day} \left(\frac{a_{ij}}{0.001 \mu\text{m}} \right)^{-2} \left(\frac{T}{1500 \text{ K}} \right)^{-\frac{1}{2}} \left(\frac{m_{ij}}{40m_{\text{H}}} \right)^{\frac{1}{2}} \left(\frac{c_{\text{tot}}}{3 \times 10^7 \text{ cm}^{-3}} \right)^{-1} \left(\frac{A_i}{5 \times 10^{-3}} \right)^{-1}$$

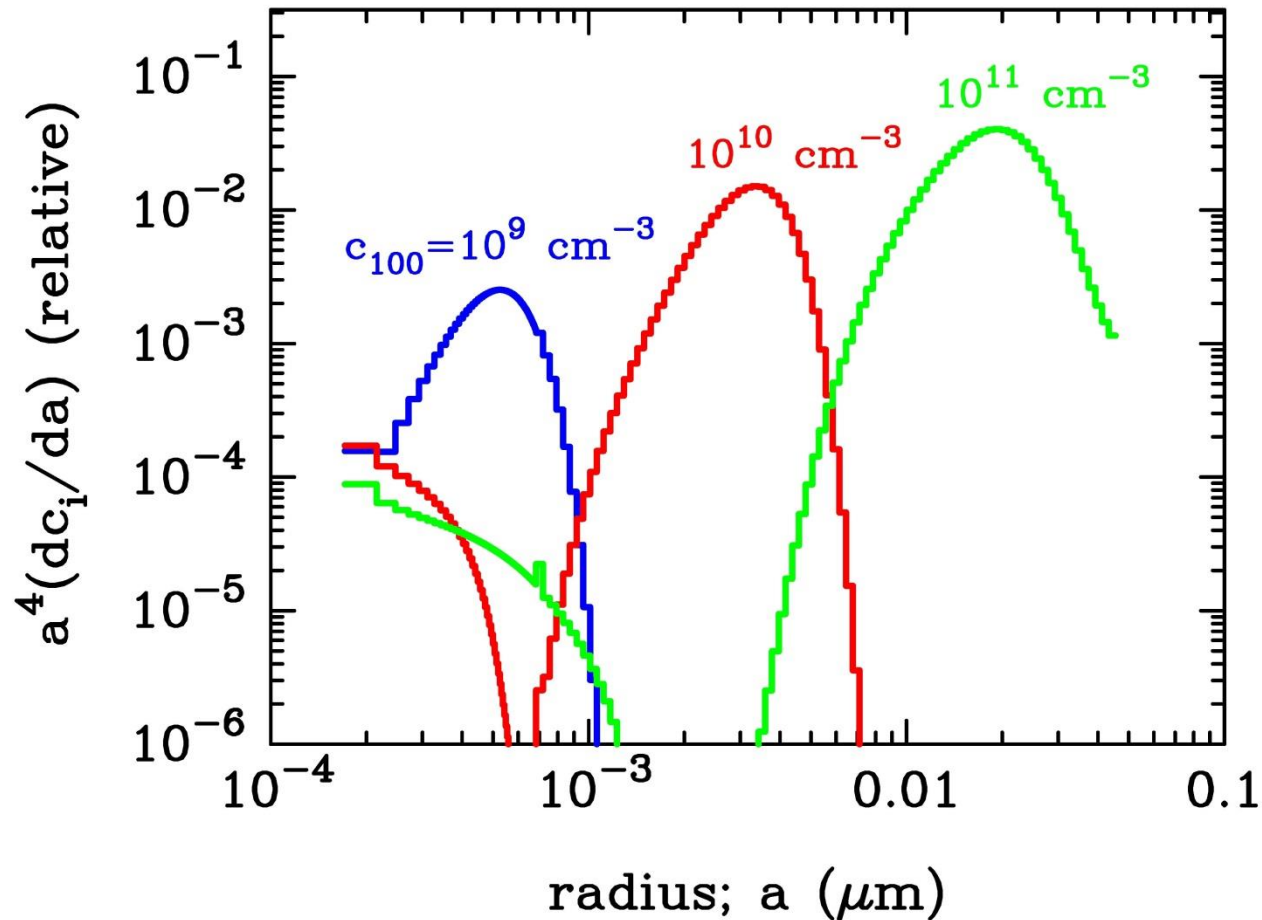
– Timescale of coagulation between 0.001 μm -sized grains

$$\tau_{\text{coag}} \simeq \tau_{\text{acc}} \left(\frac{1}{4\sqrt{2}} \right) (10^3)^{\frac{1}{2}} 10^3 \simeq 155 \text{ day}$$

– Timescale of gas expansion

$$\tau_{\text{exp}} = \left(\frac{1}{c} \left| \frac{dc}{dt} \right| \right)^{-1} = \frac{t}{3} \simeq 220 \text{ day}$$

3-6. Size distribution of SiC grains formed



- Radius of newly formed grains is larger for higher gas density
- In the density range considered in this study, grain radius is not large enough to reproduce ones observed in presolar SiC grains

4. Summary of this talk

We investigate the formation of SiC grains in the ejecta of supernovae, self-consistently treating

- **formation of SiC molecules**
- **growth of SiC grains via accretion of molecules**
- **growth of SiC grains via grain-grain coagulation**

We have realized, for the first time, the formation of SiC grains (but with small radii of $< 0.1 \mu\text{m}$...)

- ## calculations for more dense cases needed to**
- ## achieve the formation of SiC grains as large as**
- ## presolar Type-X SiC grains ($a > 0.1 \mu\text{m}$)**